

**ABSOLUTE MAXIMUM RATINGS**

SUPPLY VOLTAGE, +V <sub>S</sub> to -V <sub>S</sub>	350V
OUTPUT CURRENT, continuous	60mA
INPUT VOLTAGE, differential	±16V
INPUT VOLTAGE, common mode	±V <sub>S</sub>
TEMPERATURE, junction	150°C

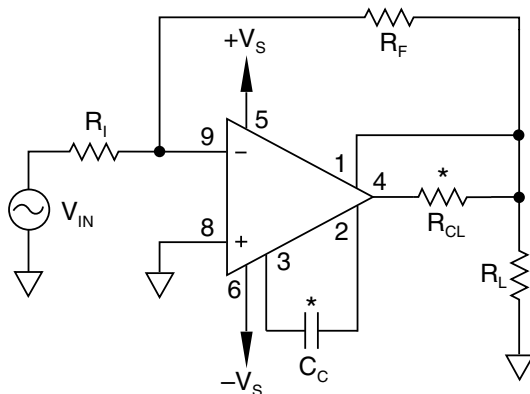
**NOTE:** Refer to parent product data sheet PA241 for typical AC electrical characteristics, precautions, applications and other test parameters.

**DC WAFER PROBED SPECIFICATIONS**

PARAMETER	TEST CONDITIONS <sup>1</sup>	MIN	TYP	MAX	UNITS
OFFSET VOLTAGE, initial	V <sub>S</sub> = ±50V		15	40	mV
BIAS CURRENT, initial			56	200	pA
COMMON MODE REJECTION	V <sub>CM</sub> = ±90 V DC	84	94		dB
VOLTAGE SWING	I <sub>O</sub> = 40mA	±V <sub>S</sub> -12	±V <sub>S</sub> -10		V
SUPPLY CURRENT, quiescent	V <sub>S</sub> = ±50 V	1.8	2.1	2.3	mA

**NOTES:** 1. Unless otherwise stated V<sub>S</sub> = ±50 V, T<sub>A</sub> = 25°C, DC input specification ± value given.  
 2. Sample tested by wafer to 95%.

**TYPICAL EXTERNAL CONNECTIONS**



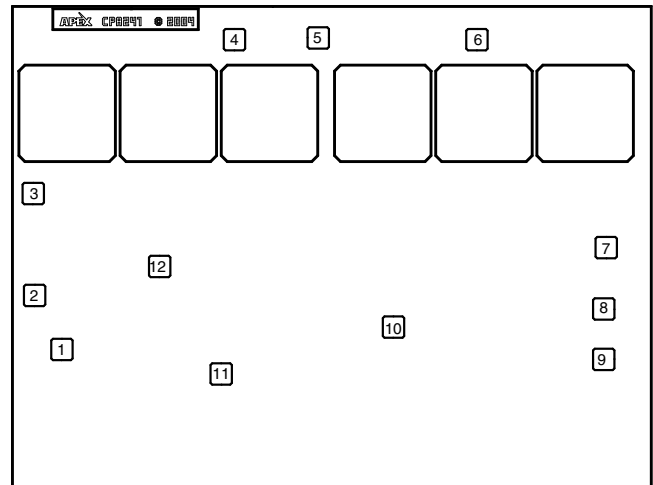
\* Required component and value if given.  
 Optional balance components are recommended values.  
 C<sub>C</sub> is NPO, rated for full supply voltage -V<sub>S</sub> to +V<sub>S</sub>.

**NOTE:** Diagram for connection illustration only.  
 All op amp configurations are possible.

Pad	Function	Pad	Function
1	Output	5	+Vs
2	Compensation	6	-Vs
3	Compensation	8	+IN
4	Current Limit	9	-IN

**CAUTION** The CPA241 is a MOSFET amplifier. ESD handling procedures must be observed

**DIE LAYOUT**



Dimension: 154.5 x 117.5 ± 2.5 Mils.  
 Thickness: 15 Mil (380μ).  
 Backside Metal: None, Silicon.  
 Bond pad: 5 Mil sq (127μ) Al.  
 Make no connection to bond pads not listed by function.

Note: The backside of the CPA241 die is isolated up to 500V. The top side walls of the CPA241 die are isolated up to 300V.

Ordering Information:  
 Order #: CPA241D180:  
 Die are only available in wafer packages with a total of 80 die per package.